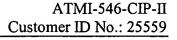
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1	FORM		Filing Date	Februar y 23, 2004							
	(to be used for all correspondence after in	nitial filing)	First Named Inventor	r Frank DiMeo, Jr.							
			Group Art Unit	2856							
,			Examiner Name	ТВА							
	Total Number of Pages in This Sub	mission	Attorney Docket Numb	ber ATMI-546-CIP II							
•		ENCLOSU	RES (check all that apply)								
	Fee Transmittal Form Fee Attached	L (for	signment Papers r an Application) awing(s)	After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences							
	Amendment / Reply	Lice	ensing-related Papers	Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)							
	After Final	Pet	ition	Proprietary Information							
	Affidavits/declaration(s)	avits/declaration(s) Petition		Status Letter							
	Extension of Time Request	Pov Cha	ver of Attorney, Revocation ange of Correspondence Iress	Other Enclosure(s) (please identify below):							
	Express Abandonment Request	Terminal Disclaimer									
	Information Disclosure Statement	Red	quest for Refund								
	Gertified Copy of Priority Document(s)	CD, Number of CD(s)									
	Response to Missing Parts/ Incomplete Application	Remarks									
Response to Missing Parts under 37 CFR 1.52 or 1.53											
	SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT										
	Firm or Individual name Margaret Chappuis, Reg. No. 45,735										
	Signature Yazar Chappus										
	Date August 31, 2004										
		CERT	IFICATE OF MAILING								
	I hereby certify that this correspondence is being	ng deposited	pursuant to 37 C.F.R. 1.8 in an	envelope addressed to:							
	Commissioner for Patents, P.O. Box 1450, Alex		2313-1450 on this date:	14-2-04							
	Type or printed name Lee Ann DiLello										

Signature





IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Frank DiMeo, Jr.

Group Art Unit: 2856

U.S. Application No.: 10/784,750

Examiner: TBA

Filed: February 23, 2004

Title: APPARATUS AND PROCESS FOR SENSING FLUORO SPECIES IN

SEMICONDUCTOR PROCESSING SYSTEMS

CERTIFICATE OF MAILING

I hereby certify that this paper or fee is being deposited pursuant to 37 CFR 1.8

on the date indicated below and is addressed to the Commissioner of Patents, P.O. Box 1450, Alexandria, VA

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

■ 1. This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required in accordance with 37 CFR § 1.56 and § 1.97(b). Please note that Reference AH "Inorganic Solid Fluorides, Chemistry and Physics" is a book and is not enclosed. Should a copy of this reference be required, Applicants will provide a copy.

2.	U.S. fi	information Disclosure Statement is being filed more than three months after the sling date AND after the mailing date of the first Office Action on the merits, but the mailing date of a Final Rejection or Notice of Allowance.
	□ a.	I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of such item by a foreign patent office in a counterpart foreign application, which occurred no more than three months prior to filing the Information Disclosure Statement. 37 C.F.R. §1.97(e)(1).
	□ b.	I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. §1.97(e)(2).
	□ c.	Attached is our check no in the amount of \$180 in payment of the fee under 37 C.F.R. §1.17(p). Please credit or debit Deposit Account No. 50-0860 as needed to ensure consideration of the disclosed information. Two duplicate copies of this paper are attached.
3.	U.S. fi but be: Disclo \$130.0 Depos:	information Disclosure Statement is being filed more than three months after the dling date and after the mailing date of a Final Rejection or Notice of Allowance, fore payment of the Issue Fee. Applicant(s) hereby petition(s) that the Information sure Statement be considered. Attached is our check no in the amount of 0 in payment of the petition fee under 37 C.F.R. §1.17(i)(1). Please credit or debit it Account No as needed to ensure consideration of the disclosed information. uplicate copies of this paper are attached.
	□ a.	I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of such item by a foreign patent office in a counterpart foreign application which occurred no more than three months prior to filing the Information Disclosure Statement. 37 C.F.R. §1.97(e)(1).
	□ b.	I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. §1.97(e)(2).
4.	(other)	:

Applicant does not believe that any additional fee is due in connection with the foregoing. However, any deficiencies may be charged to the deposit account 50-0860.

Respectfully submitted,

August Chapping

Margaret Chappuis

Registration No. 45,735

Agent for Applicant

7 Commerce Drive Danbury, CT 06810

Date: 8/31/2004 Advanced Technology Materials, Inc.

Agent Ref: ATMI-546-CIP-II

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EP 0 7 2004	Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT			ATMI-546-CIP-II		10/784,750				
l 6				APPLICANT						
INFORMAN ENT & TRANS				Frank DiMeo, Jr.						
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				February 23, 2004	2856					
			U.S.	PATENT DOCUMENTS						
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING IF APPRO			
	AA	10/273,036		Frank DiMeo, et al.			10/17/200	2		
	AB	6,265,222	6/24/2001	Frank DiMeo, Jr., et al.						
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:		NUMBER	DATE	COUNTRY	CLASS	SUBCLAS S	YES	NO		
							X (abstract only)			
	- L	OTHER DOCUM	MENTS (Includ	ing Author, Title, Journal-D	ate. Page N	lumber Etc.)	Omy)			
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	AH Ed P. Hagenmuller, Inorganic Solid Fluorides, Chemistry and Physics, Academic Press, 1985. (See Information Disclosure Statement Box 1)									
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citation if no	t in cor	normance and not	considered. Inc.	lude copy of this form with nex	tt communi	cation to the a	pplicant.			